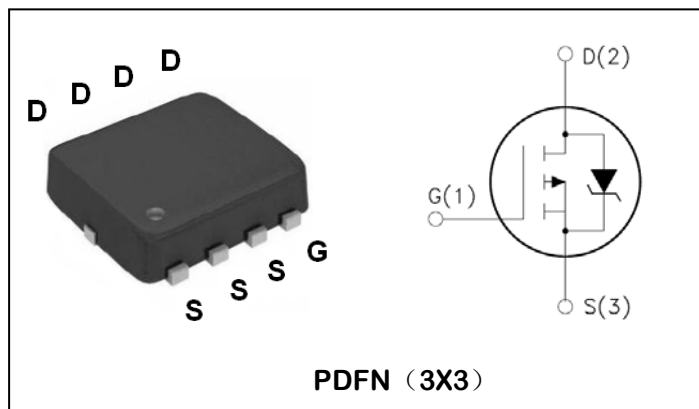


P-Channel Logic Level Enhancement Mode Field Effect Transistor**PRODUCT SUMMARY**

V_{DSS}	I_D	$R_{DS(ON)}$ (m Ω)
-30V	-40A	10m Ω

Features:

- Low Gate Charge for Fast Switching Application
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- Reliable and Rugged

**Absolute Maximum Ratings** ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Ratings	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	-40	A
Mounted on Large Heat Sink				
I _{DM}	300μs Pulse Drain Current Tested ⁽²⁾	T _C =25°C, V _{GS} =-10V	-120	A
I _D	Continuous Drain Current ⁽¹⁾	T _C =25°C, V _{GS} =-10V	-40	A
		T _C =100°C V _{GS} =-10V	-26	A
P _D	Maximum Power Dissipation	T _C =25°C	25.6	W

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R_{thJC}	Thermal resistance junction-case max ⁽¹⁾	4.9	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance junction-ambient max ⁽¹⁾	62	$^\circ\text{C/W}$

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
On/off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250uA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -27V, V _{GS} =0V T _J =25°C	--	--	-1	uA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250uA	-1.0	-1.6	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
R _{DS(ON)}	Drain-SourceOn-stateResistance ⁽²⁾	V _{GS} = -10V, I _{DS} =-20A	--	7.5	10	mΩ
		V _{GS} = -4.5V, I _{DS} =-10A	--	11.6	16	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0V,	--	3564	--	pF
C _{oss}	Output Capacitance	V _{DS} = -15V,	--	416	--	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	--	373	--	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time(1)	V _{DD} =-15V,	--	16	--	ns
t _r	Turn-on Rise Time(1)	I _D = -20A, V _{GS} = -10V,	--	21	--	
t _{d(OFF)}	Turn-off Delay Time(1)	R _{GEN} =2.5 Ω	--	68	--	
t _f	Turn-off Fall Time(1)		--	52	--	
Q _g	Total Gate Charge(1)	V _{DS} =-15V, V _{GS} = -10V,	--	37	--	nC
Q _{gs}	Gate-Source Charge(1)	I _{DS} =-20A	--	6.5	--	
Q _{gd}	Gate-Drain Charge(1)		--	9.4	--	
Avalanche Characteristics						
EAS	Single Pulse Avalanche Energy ⁽³⁾	V _{DD} =-15V,L=0.5mH ,V _{GS} =10V,R _g =25 Ω , V _{GS} =-10V	121	--	--	mJ
Diode Characteristics						
V _{SD}	Diode Forward Voltage ⁽²⁾	I _{SD} =-30A, V _{GS} =0V,T _J =25°C	--	-0.8	-1.2	V

NOTES:

1. Surface Mounted on FR4 Board, t ≤ 10 sec.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The Min. value is 100% EAS tested guarantee.

Typical Performance Characteristics

Figure 1: Output Characteristics

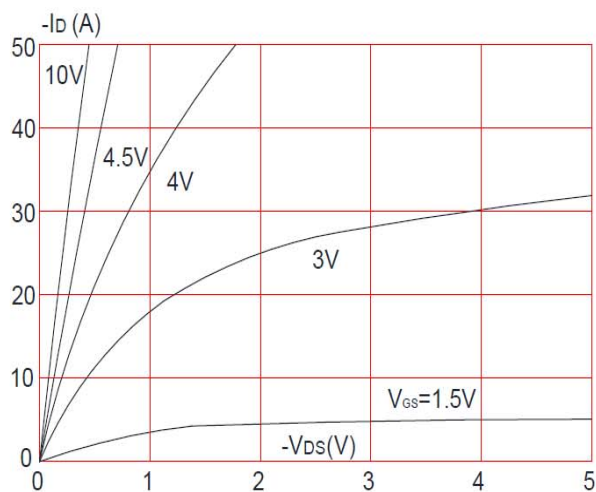


Figure 2: Typical Transfer Characteristics

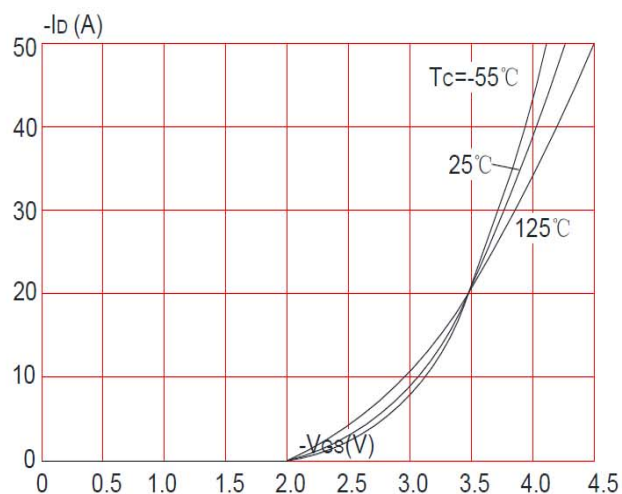


Figure 3: On-resistance vs. Drain Current

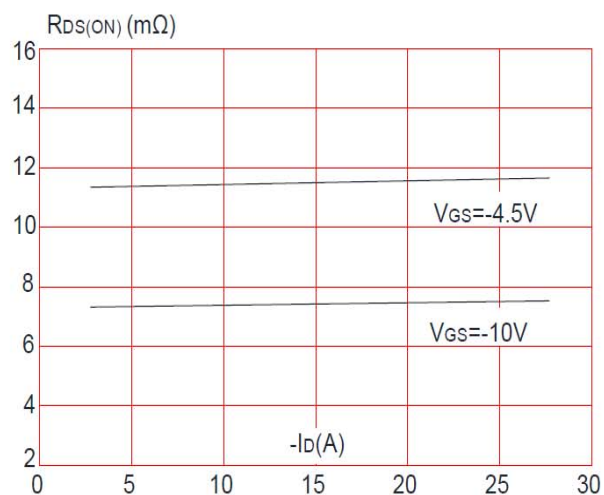


Figure 4: Body Diode Characteristics

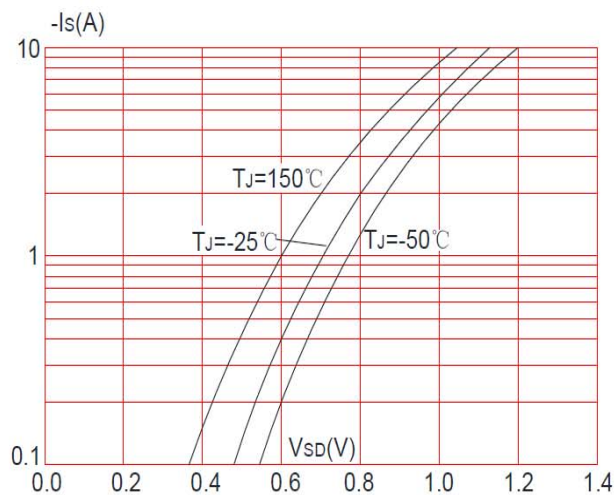


Figure 5: Gate Charge Characteristics

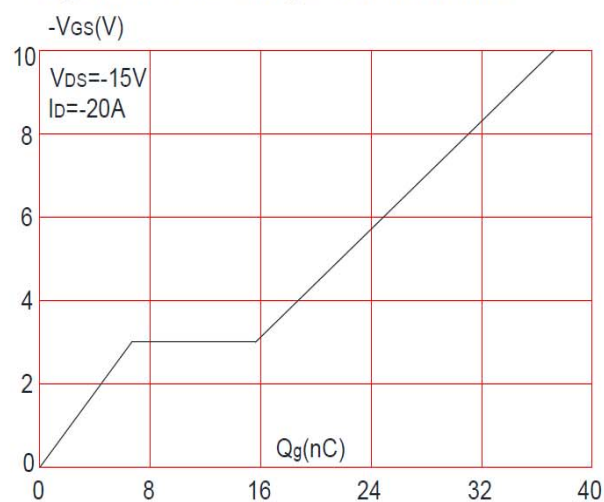


Figure 6: Capacitance Characteristics

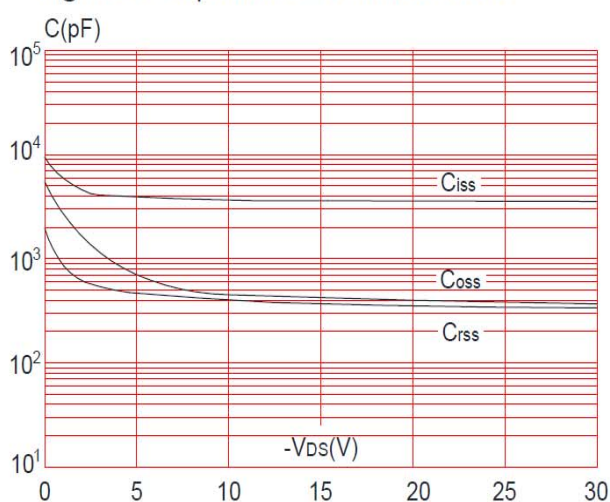


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

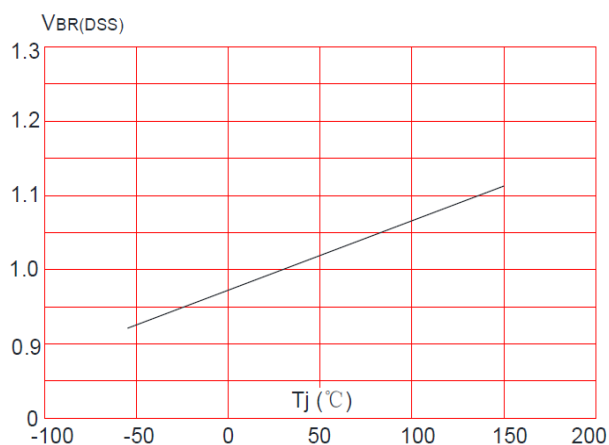


Figure 8: Normalized on Resistance vs. Junction Temperature

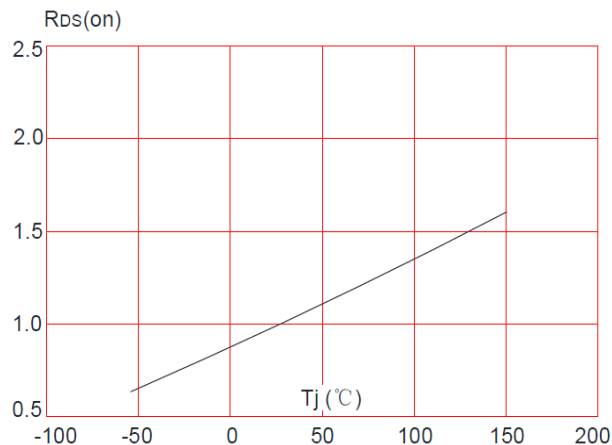


Figure 9: Maximum Safe Operating Area

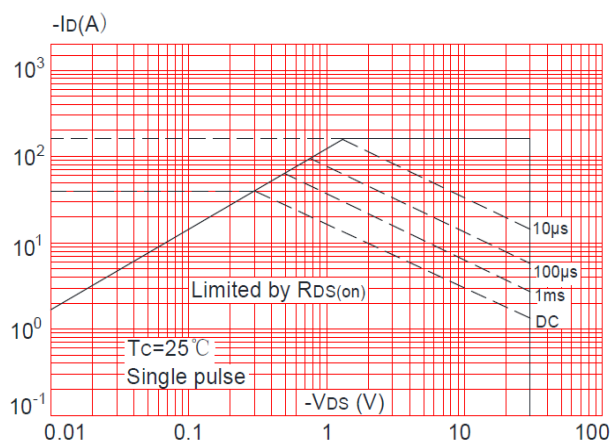


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

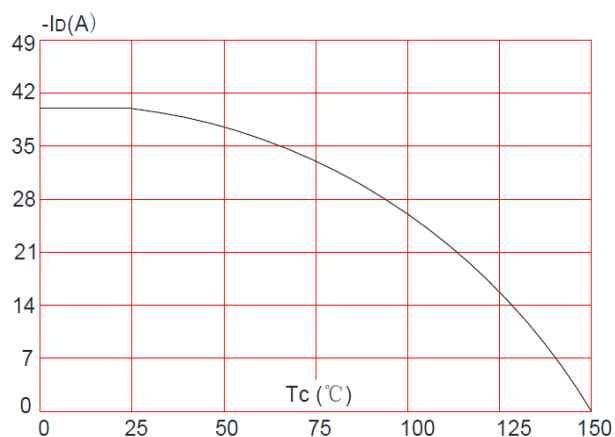
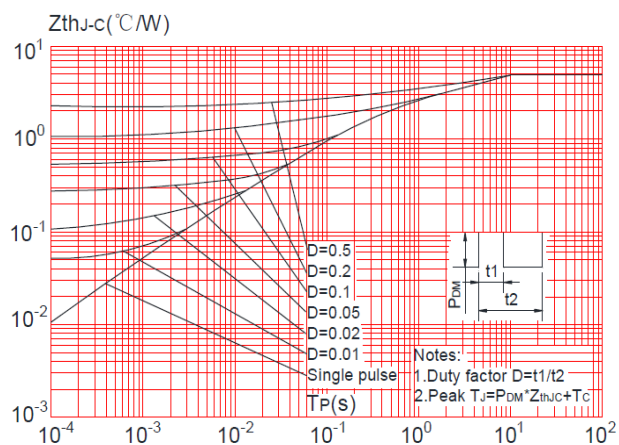
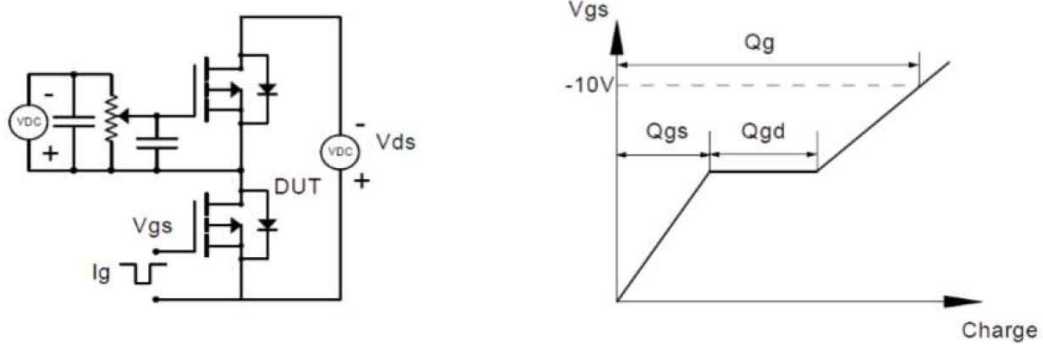


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

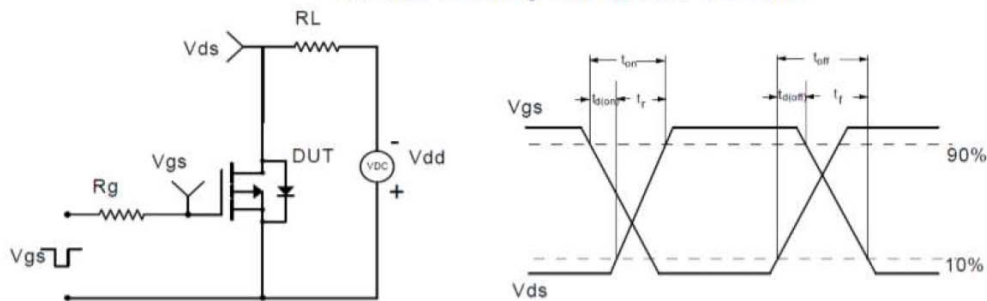


Test Circuit

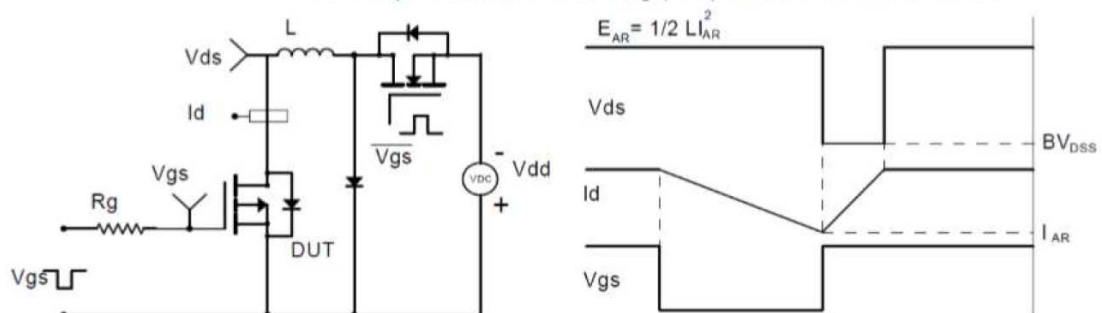
Gate Charge Test Circuit & Waveform



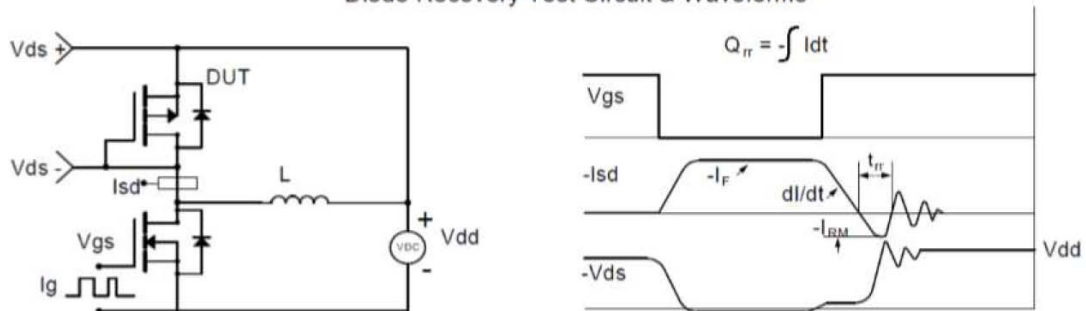
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

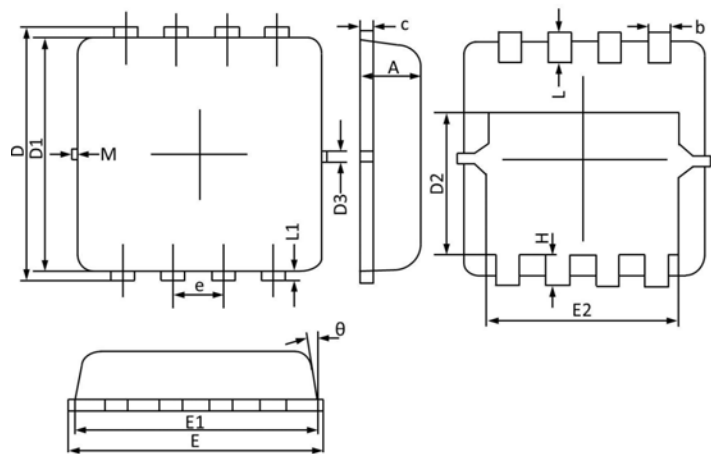


Diode Recovery Test Circuit & Waveforms



PACKAGE MECHANICAL DATA

PDFN (3X3) Package Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.850	0.028	0.034
b	0.200	0.400	0.008	0.016
c	0.100	0.250	0.004	0.009
D	3.150	3.450	0.124	0.135
D1	3.000	3.250	0.119	0.128
D2	1.580	1.980	0.062	0.077
D3	0.130REF		0.005REF	
E	3.150	3.450	0.124	0.135
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
H	0.300	0.500	0.011	0.019
M	0.150REF		0.006REF	
e	0.650 TYP.		0.026 TYP.	
L	0.300	0.500	0.011	0.019
L1	0.130REF		0.005REF	
θ	0°	12°	0°	12°

Making Diagram

D

D

D

D

M40P03Z

YMXX XX

S

S

S

G

ADM40N03Z:Part number

X:Internal control code

H:Halogen Free

Y:Year

M:Month

Ordering information

Part number	Package	Marking	Packing	Quantity
ADM40P03Z	PDFN3x3	M40P03Z	Tape&reel	5000pcs

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